

# BCR8PM-12LG

# Triac

Medium Power Use

REJ03G1508-0100 Rev.1.00 Feb 14, 2007

### **Features**

•  $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGT III}$ : 30 mA

V<sub>iso</sub>: 2000 V

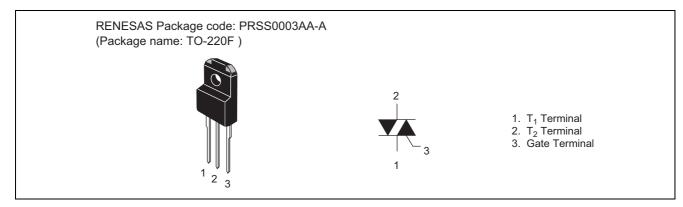
• The Product guaranteed maximum junction temperature 150°C

• Insulated Type

Planar Type

• UL Recognized : Yellow Card No. E223904 File No.E80271

### **Outline**



# **Applications**

Switching mode power supply, light dimmer, electronic flasher unit, Television, Stereo system, refrigerator, Washing machine, infrared kotatsu, and carper, solenoid driver, small motor control, copying machine, electric tool, electric heater control, and other general purpose control applications

Parameter	Symbol	Voltage class	Unit
Parameter	Symbol	12	
Repetitive peak off-state voltage Note1	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V



### BCR8PM-12LG

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	8	A	Commercial frequency, sine full wave 360°conduction, Tc = 107°C
Surge on-state current	I <sub>TSM</sub>	80	Α	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusion	l <sup>2</sup> t	26	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak gate voltage	$V_{GM}$	10	<b>V</b>	
Peak gate current	I <sub>GM</sub>	2	Α	
Junction Temperature	Tj	-40 to +150	°C	
Storage temperature	Tstg	-40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	V <sub>iso</sub>	2000	V	Ta = 25°C, AC 1 minute, $T_1 \bullet T_2 \bullet G$ terminal to case

Notes: 1. Gate open.

# **Electrical Characteristics**

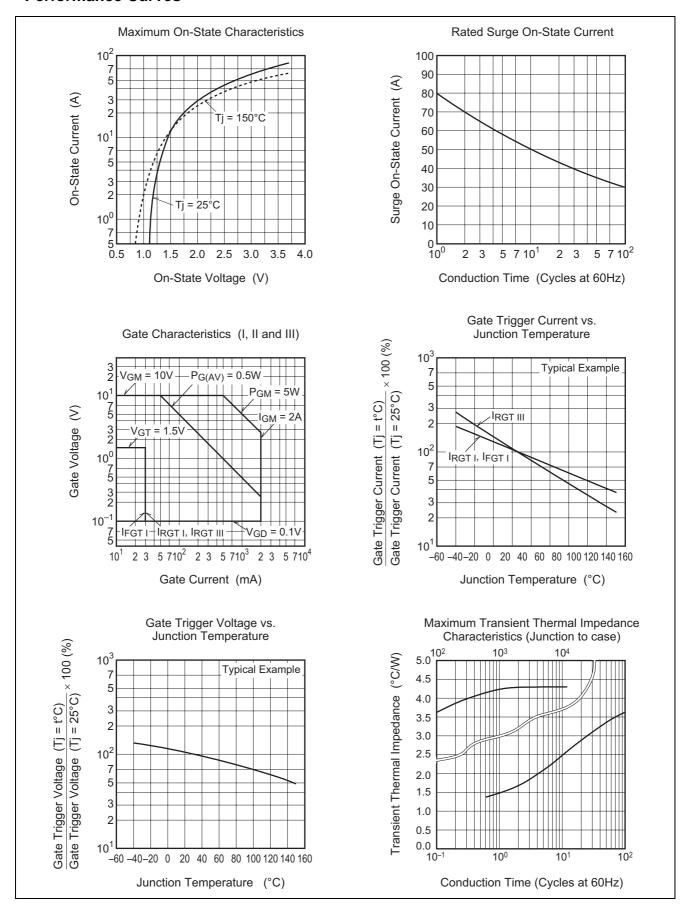
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0	mA	Tj = 150°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	1.6	V	Tc = 25°C, I <sub>TM</sub> = 12 A,
							instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGT_{I}}$		_	1.5	V	Tj = 25°C, $V_D$ = 6 V, $R_L$ = 6 Ω,
	II	$V_{RGT_{I}}$	_	_	1.5	V	$R_G = 330 \Omega$
	III	$V_{RGT_{III}}$	_	_	1.5	V	
Gate trigger curent <sup>Note2</sup>	I	$I_{FGTI}$	_	_	30	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	$I_{RGTI}$	_	_	30	mA	$R_G = 330 \Omega$
	III	I <sub>RGTIII</sub>	_	_	30	mA	
Gate non-trigger voltage		$V_{\sf GD}$	0.2/0.1	_	_	V	$Tj = 125$ °C/150°C, $V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	_	_	4.3	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutation voltage Note4		(dv/dt)c	10/1	_	_	V/µs	Tj = 125°C/150°C

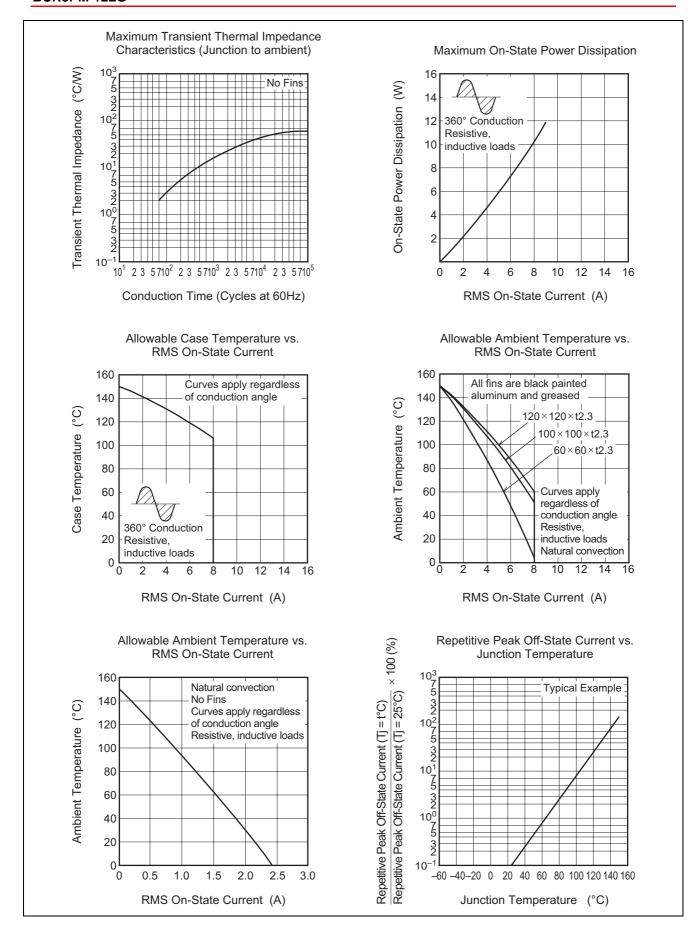
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

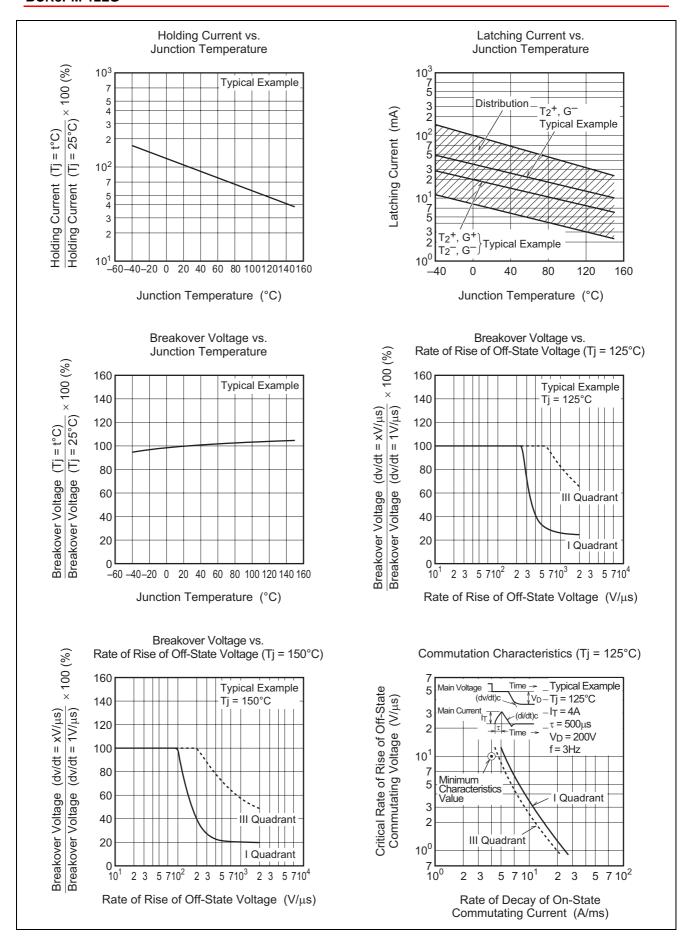
- 3. The contact thermal resistance  $R_{th\;(j\text{-}c)}$  in case of greasing is  $0.5^{\circ}\text{C/W}.$
- 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

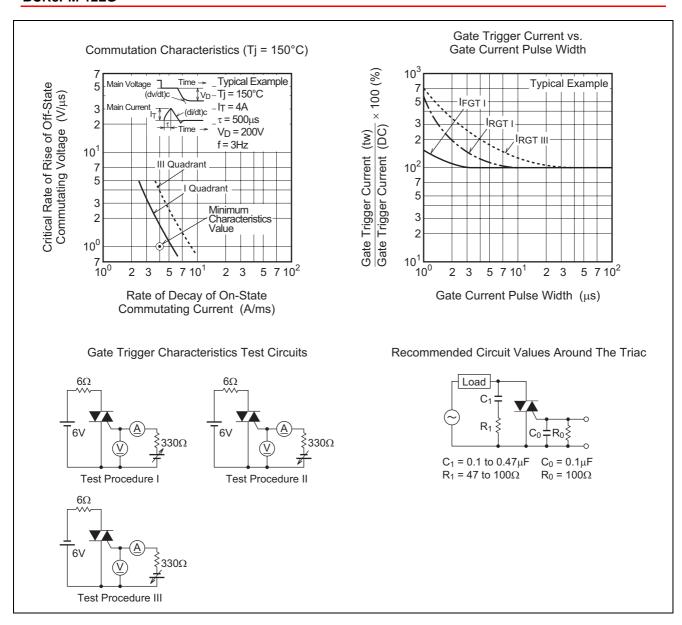
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C	Supply Voltage
2. Rate of decay of on-state commutating current (di/dt)c = -4.0 A/ms	Main Current (di/dt)c
3. Peak off-state voltage V <sub>D</sub> = 400 V	Main Voltage Time

## **Performance Curves**

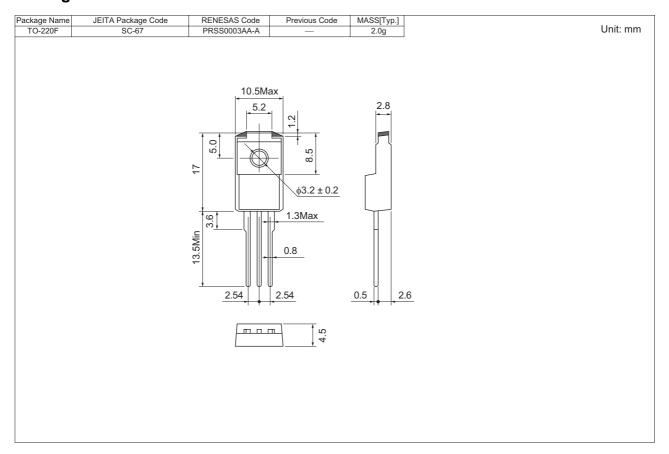








# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR8PM-12LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR8PM-12LG-A8

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510